

100N10

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N-Channel PowerTrench[®] MOSFET

100V, 75A, 10mΩ

Features

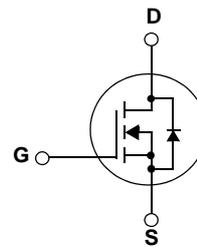
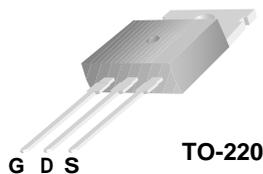
- $R_{DS(on)} = 8.2m\Omega$ (Typ.) @ $V_{GS} = 10V, I_D = 75A$
- Fast switching speed
- Low gate charge
- High performance trench technology for extremely low $R_{DS(on)}$
- High power and current handling capability
- RoHS compliant

Applications

DC to DC converters / Synchronous Rectification

Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted*

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	100	V
V_{GSS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous ($T_C = 75^\circ\text{C}$)	75	A
I_{DM}	Drain Current - Pulsed (Note 1)	300	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	365	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.8	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	208 1.4	W W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.72	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case to Sink Typ.	0.5	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

*When mounted on the minimum pad size recommended (PCB Mount)

Package Marking and Ordering Information $T_C = 25^\circ\text{C}$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP100N10	FDP100N10	TO-220	-	-	50

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$, $T_J = 25^\circ\text{C}$	100	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, Referenced to 25°C	-	0.1	-	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 100\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
		$V_{DS} = 100\text{V}$, $V_{GS} = 0\text{V}$, $T_J = 150^\circ\text{C}$	-	-	500	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	2.5	-	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 75\text{A}$	-	8.2	10	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{V}$, $I_D = 37.5\text{A}$ (Note 4)	-	110	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	5500	7300	pF
C_{oss}	Output Capacitance		-	530	710	pF
C_{riss}	Reverse Transfer Capacitance		-	220	325	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 50\text{V}$, $I_D = 75\text{A}$ $V_{GS} = 10\text{V}$ (Note 4, 5)	-	76	100	nC
Q_{gs}	Gate to Source Gate Charge		-	30	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	20	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{V}$, $I_D = 75\text{A}$ $V_{GS} = 10\text{V}$, $R_{GEN} = 25\Omega$ (Note 4, 5)	-	70	150	ns
t_r	Turn-On Rise Time		-	265	540	ns
$t_{d(off)}$	Turn-Off Delay Time		-	125	260	ns
t_f	Turn-Off Fall Time		-	115	240	ns

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	75	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	300	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_{SD} = 75\text{A}$	-	-	1.25	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{V}$, $I_{SD} = 75\text{A}$	-	71	-	ns
Q_{rr}	Reverse Recovery Charge	$di_f/dt = 100\text{A}/\mu\text{s}$ (Note 4)	-	164	-	nC

Notes:

- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: $L = 0.13\text{mH}$, $I_{AS} = 75\text{A}$, $V_{DD} = 25\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
- 3: $I_{SD} \leq 75\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
- 4: Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
- 5: Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

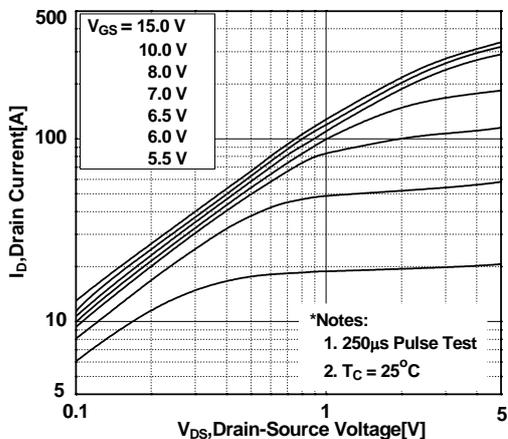


Figure 2. Transfer Characteristics

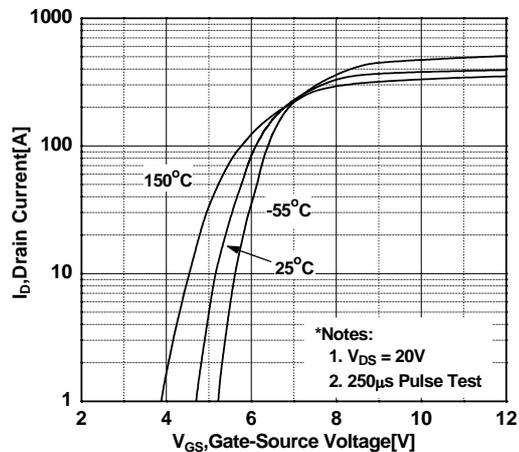


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

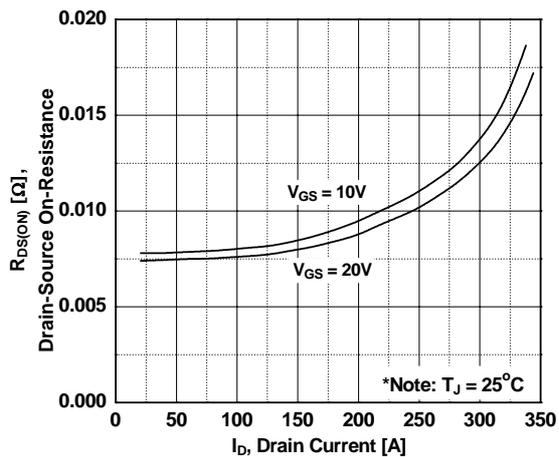


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

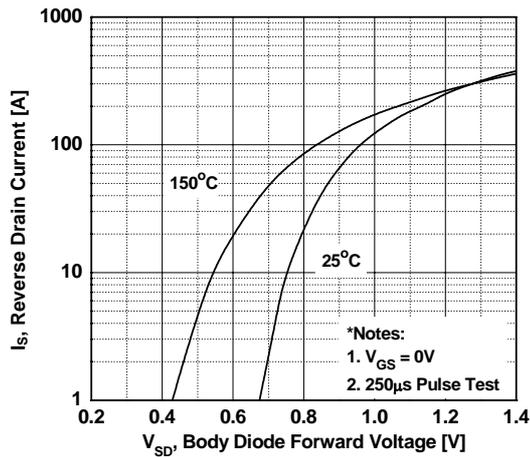


Figure 5. Capacitance Characteristics

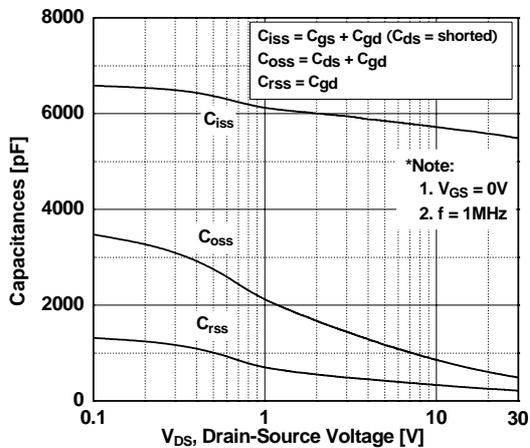
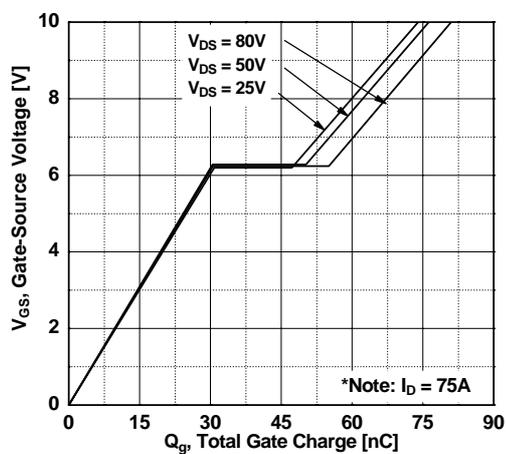


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

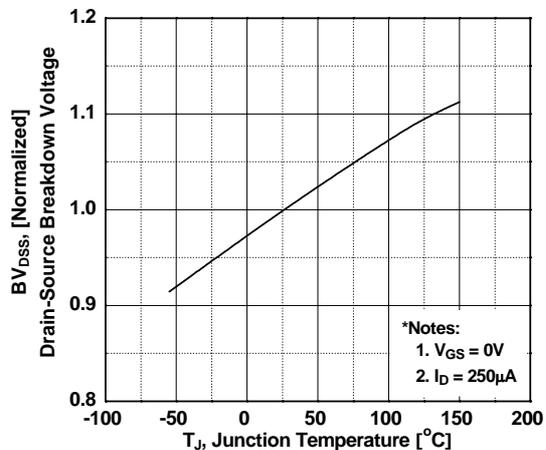


Figure 8. On-Resistance Variation vs. Temperature

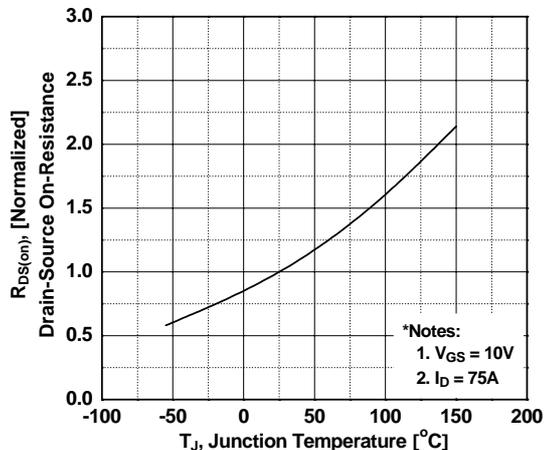


Figure 9. Maximum Safe Operating Area

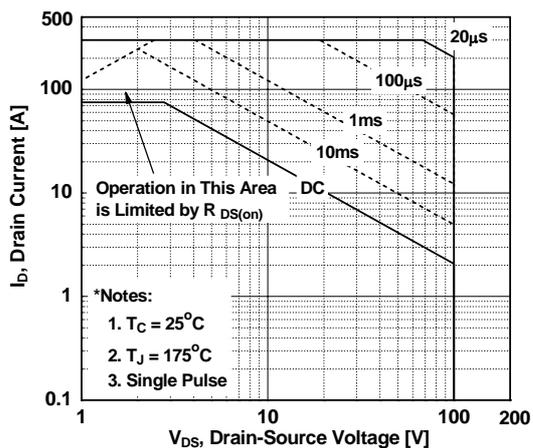


Figure 10. Maximum Drain Current vs. Case Temperature

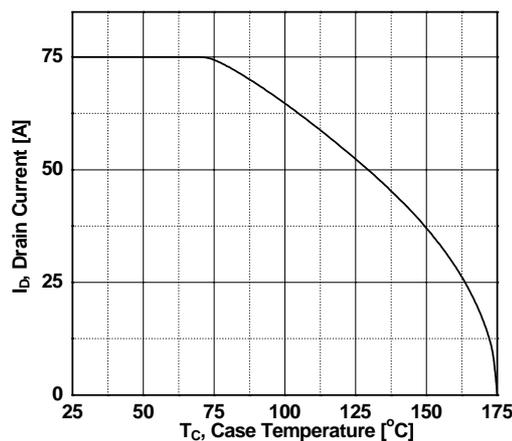


Figure 11. Transient Thermal Response Curve

